

LISTING of CLAIMS

13. (Currently amended) A process for removing photoresist sidewall residue after drywall etching of a semiconductor wafer comprising treating ~~a the~~ wafer after dry etching with a solution comprising sulfuric acid ~~and a~~ ~~mixture of~~ a fluorine containing compound and hydrogen peroxide, wherein said solution contacts said sidewall residue effectively to remove it from said dry etched wafer.
14. (Previously presented) A process for removing photoresist according to claim 13, wherein the photoresist is g-line, i-line, deep UV, E-beam or X-ray.
15. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated at a temperature of from 0 to 140 degrees C.
16. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated for 10 minutes.
17. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the operation pressure is maintained at 1 atm.
18. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the etch rate of the wafer is less than 1 Å/min.
19. (Previously presented) A process for removing photoresist after dry etching according to claim 15, wherein the wafer is treated at a temperature of 120 degrees C.

20. (Previously presented) A process for removing photoresist after drywall etching according to claim 13, wherein the fluorine containing compound is hydrofluoric acid.
21. (Previously presented) A process for removing photoresist after drywall etching according to claim 20, wherein the ratio of sulfuric acid to hydrofluoric acid and hydrogen peroxide is 3:1 by volume.
22. (New) A process according to claim 13, wherein the fluorine containing compound consists essentially of cations with a valence of +1.
23. (New) A process according to claim 13, wherein the fluorine containing compound consists of cations with a valence of +1.